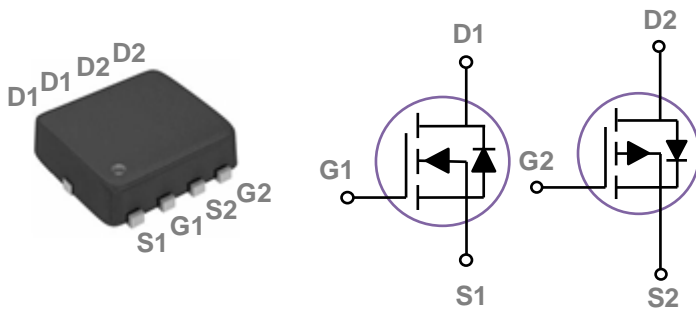


General Description

These N+P dual Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

PPAK3X3 Dual NEP Pin Configuration



BVDSS	RDSON	ID
30V	20mΩ	8A
-30V	55mΩ	-4.8A

Features

- Fast switching
- Green Device Available
- Suit for 4.5V Gate Drive Applications

Applications

- DC Fan
- Motor Drive Applications
- Networking
- Half / Full Bridge Topology

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating		Units
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	8	-4.8	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	5.1	-3	A
I_{DM}	Drain Current – Pulsed ¹	32	-19.2	A
EAS	Single Pulse Avalanche Energy ^{2,6}	14	5	mJ
IAS	Single Pulse Avalanche Current ²	17	10	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	2.5		W
	Power Dissipation – Derate above 25°C	0.016		W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150		$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150		$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	$^\circ\text{C}/\text{W}$

N-CH Electrical Characteristics (T_J=25 °C, unless otherwise)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =125°C	---	---	10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =8A	---	15	20	mΩ
		V _{GS} =4.5V , I _D =6A	---	21	30	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4	---	mV/°C
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =6A	---	13	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3, 4}	V _{DS} =15V , V _{GS} =10V , I _D =6A	---	9.2	12	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	1	1.4	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	2.1	4	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =15V , V _{GS} =10V , R _G =6Ω I _D =1A	---	2.8	5	ns
T _r	Rise Time ^{3, 4}		---	7.2	14	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	15.8	30	
T _f	Fall Time ^{3, 4}		---	4.6	9	
C _{iss}	Input Capacitance	V _{DS} =25V , V _{GS} =0V , F=1MHz	---	345	500	pF
C _{oss}	Output Capacitance		---	55	80	
C _{rss}	Reverse Transfer Capacitance		---	32	55	
R _g	Gate resistance	V _{GS} =0V , V _{DS} =0V , F=1MHz	---	3.2	6.4	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V , Force Current	---	---	8	A
I _{SM}	Pulsed Source Current		---	---	16	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =1A , T _J =25°C	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=17A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

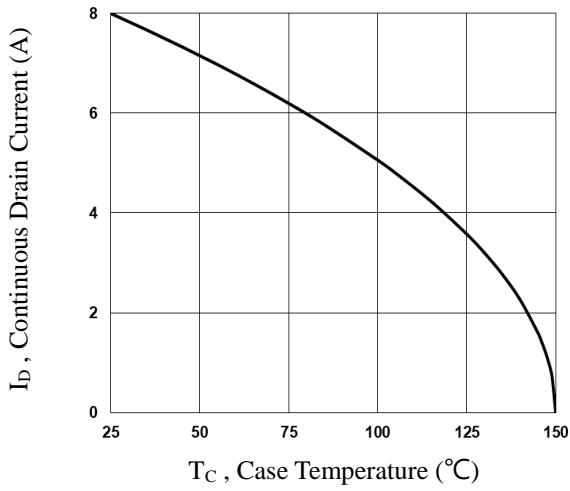


Fig.1 Continuous Drain Current vs. T_c

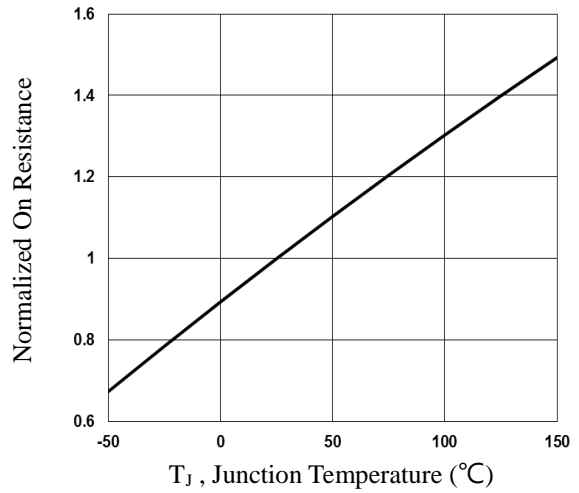


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

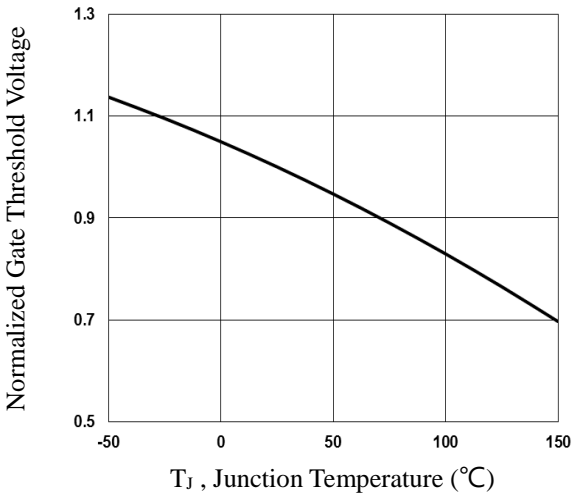


Fig.3 Normalized V_{th} vs. T_j

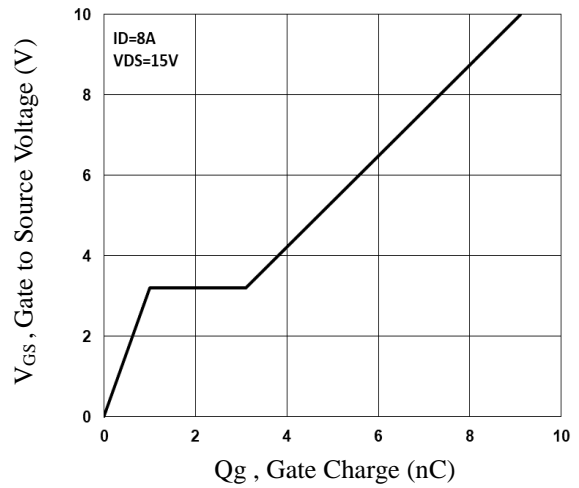


Fig.4 Gate Charge Waveform

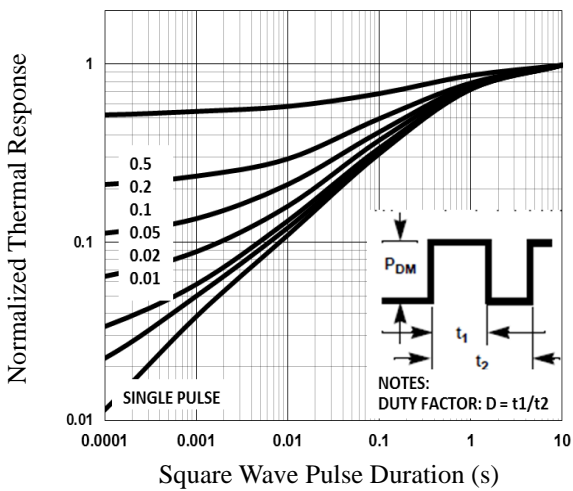


Fig.5 Normalized Transient Response

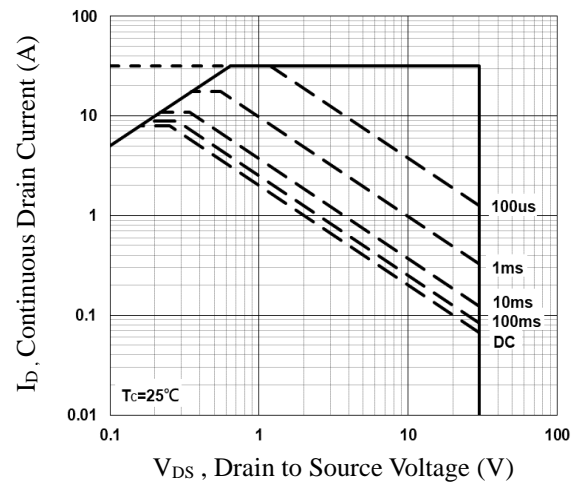


Fig.6 Maximum Safe Operation Area

P-CH Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	---	---	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-30V, V_{GS}=0V, T_J=25^\circ C$	---	---	-1	μA
		$V_{DS}=-24V, V_{GS}=0V, T_J=125^\circ C$	---	---	-10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-4A$	---	45	55	$m\Omega$
		$V_{GS}=-4.5V, I_D=-3A$	---	60	75	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.2	-1.6	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4	---	$mV/^\circ C$
g_{fs}	Forward Transconductance	$V_{DS}=-10V, I_D=-3A$	---	3.5	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{7,8}	$V_{DS}=-15V, V_{GS}=-10V, I_D=-3A$	---	11.3	7	nC
Q_{gs}	Gate-Source Charge ^{7,8}		---	2	3	
Q_{gd}	Gate-Drain Charge ^{7,8}		---	2.2	4	
$T_{d(on)}$	Turn-On Delay Time ^{7,8}	$V_{DD}=-15V, V_{GS}=-10V, R_G=6\Omega$ $I_D=-1A$	---	3.4	6	ns
T_r	Rise Time ^{7,8}		---	10.8	21	
$T_{d(off)}$	Turn-Off Delay Time ^{7,8}		---	26.9	51	
T_f	Fall Time ^{7,8}		---	6.9	13	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, F=1MHz$	---	560	810	pF
C_{oss}	Output Capacitance		---	55	80	
C_{rss}	Reverse Transfer Capacitance		---	40	60	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	-4.8	A
I_{SM}	Pulsed Source Current		---	---	-9.6	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=-1A, T_J=25^\circ C$	---	---	-1	V

Note :

5. Repetitive Rating : Pulsed width limited by maximum junction temperature.
6. $V_{DD}=-25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-10A., R_G=25\Omega, \text{Starting } T_J=25^\circ C$
7. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
8. Essentially independent of operating temperature.

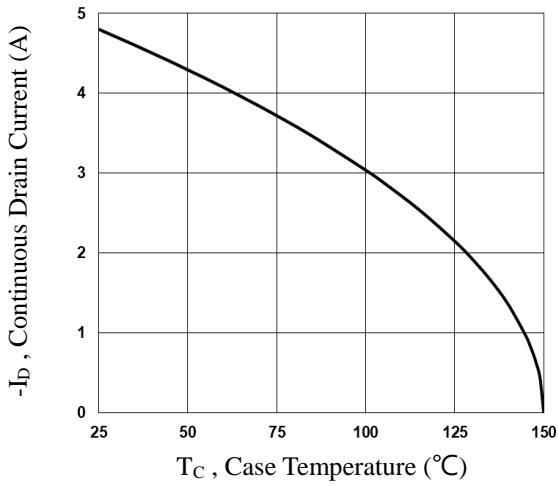


Fig.7 Continuous Drain Current vs. T_c

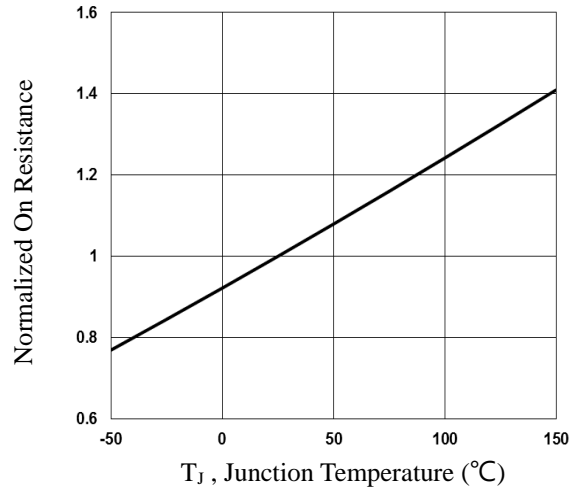


Fig.8 Normalized $R_{DS(on)}$ vs. T_j

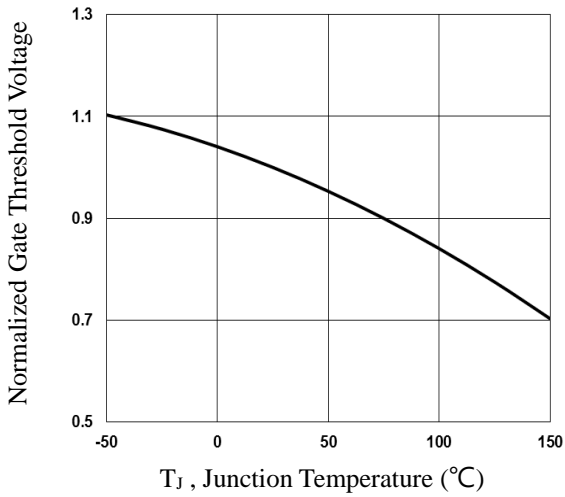


Fig.9 Normalized V_{th} vs. T_j

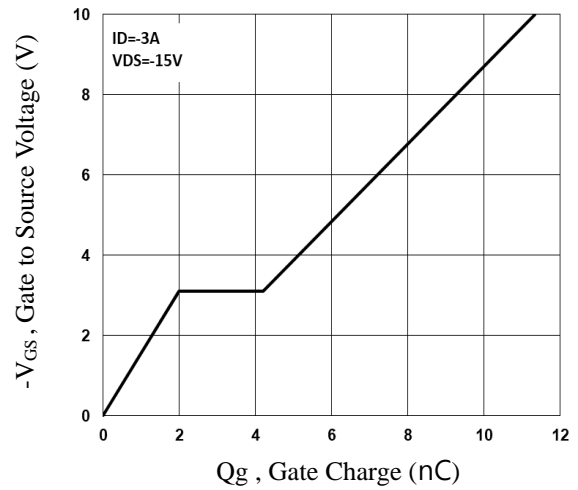


Fig.10 Gate Charge Waveform

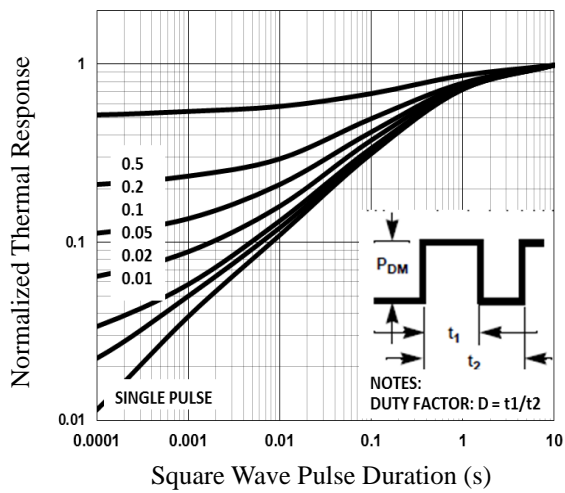


Fig.11 Normalized Transient Impedance

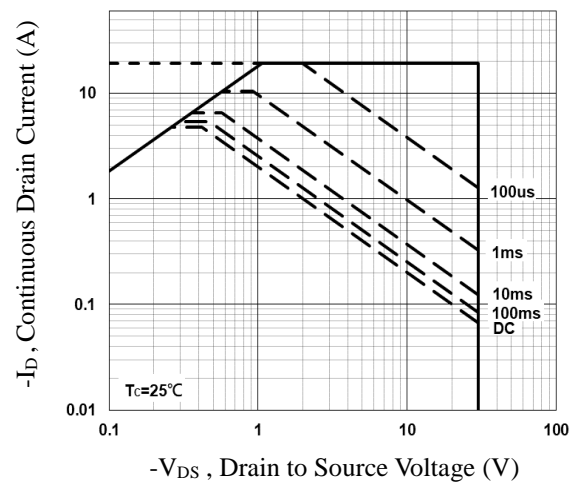
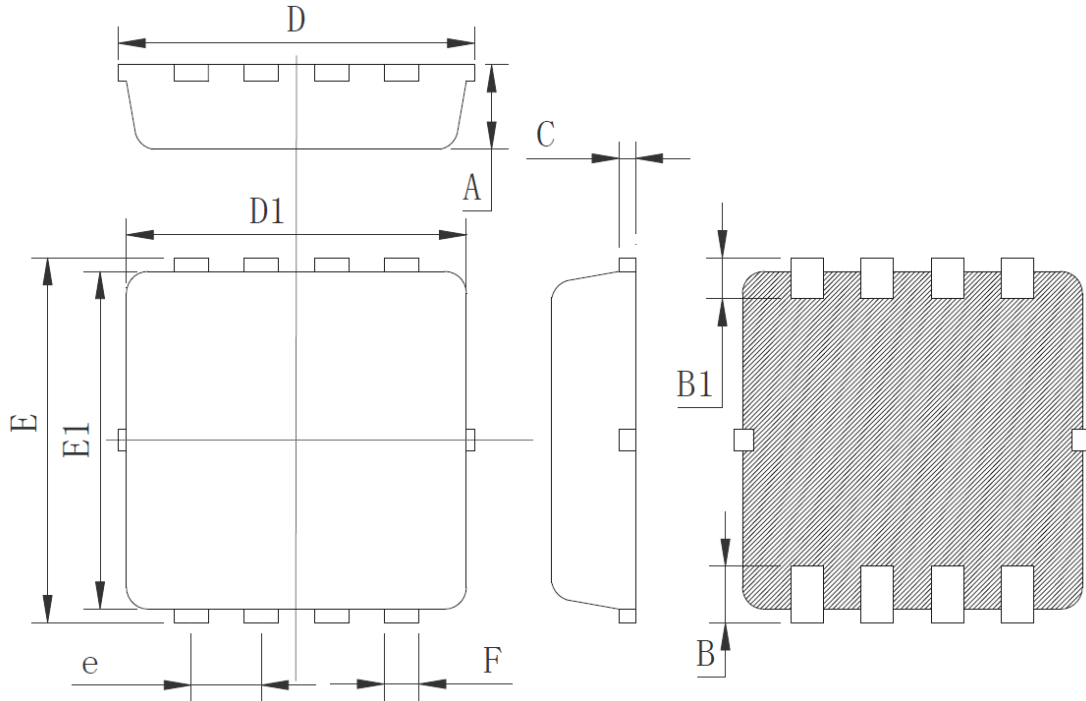


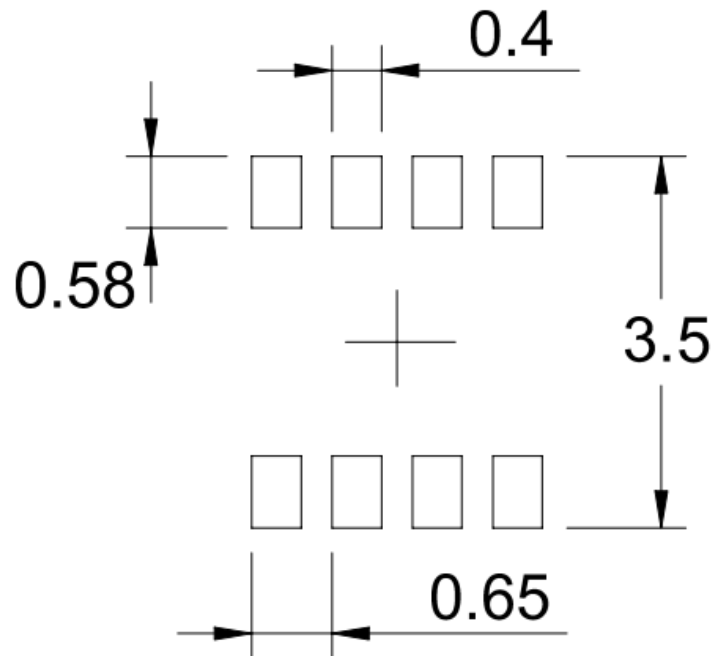
Fig.12 Maximum Safe Operation Area

PPAK3x3 Dual NEP PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.725	0.825	0.029	0.032
B	0.280	0.480	0.011	0.019
B1	0.200	0.400	0.008	0.016
C	0.130	0.200	0.005	0.008
D	3.200	3.350	0.126	0.132
D1	3.050	3.250	0.120	0.128
E	3.250	3.450	0.128	0.136
E1	3.000	3.200	0.118	0.126
e	0.650 BSC		0.026 BSC	
F	0.270	0.370	0.106	0.015

PPAK3X3 Dual NEP RECOMMENDED LAND PATTERN



unit : mm